

Electronic Supplementary Information (ESI) for “Ultralow and anisotropic thermal conductivity in semiconductor As_2Se_3 ”

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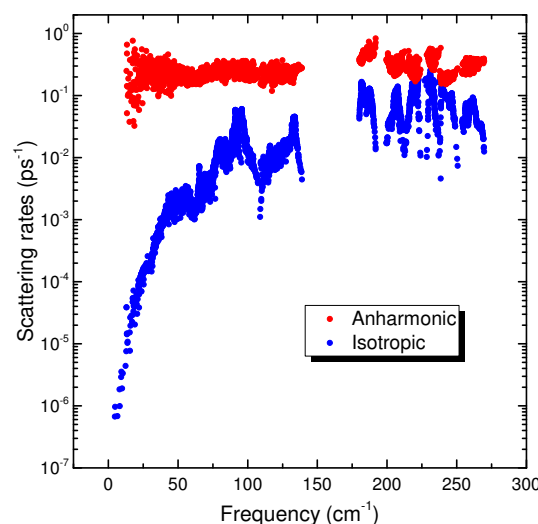


Fig. S1: Anharmonic and isotropic scattering rates vs. frequency for As_2Se_3 .

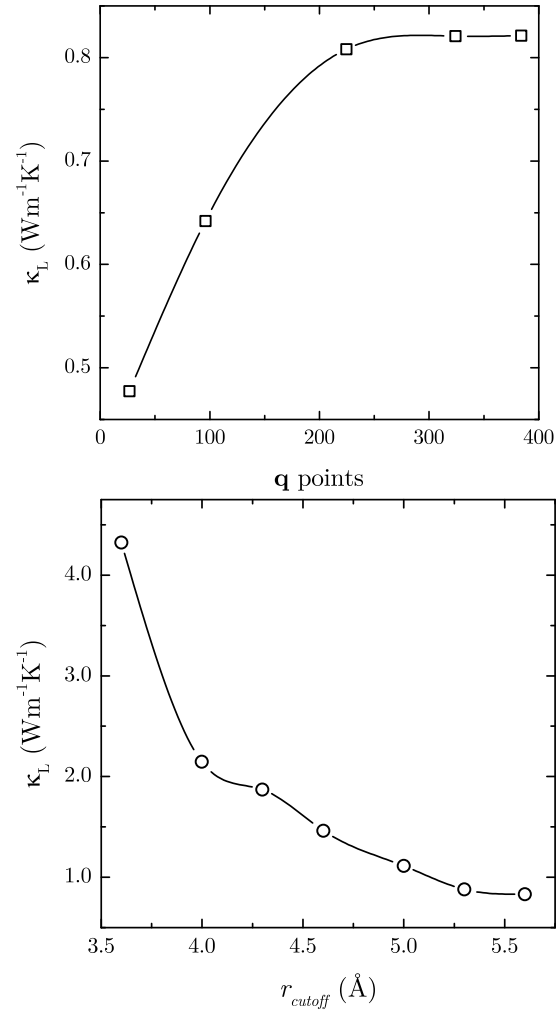


Fig. S2: Calibration curves for the number of q points (a) and cutoff radius (b) used to calculate the third-order IFCs of As_2Se_3 .